ABSTRACT

Embodiments of the present disclosure relate to the field of semiconductors, and provide a method for manufacturing a semiconductor structure and a semiconductor structure. The method at least includes: providing a base substrate, and forming a stack structure on the base substrate; etching the stack structure to form a first capacitor hole; forming a first initial electrode layer, a second electrode layer, and a third electrode layer sequentially in the first capacitor hole, where an oxidation resistance of the second electrode layer is greater than oxidation resistances of the first initial electrode layer and the third electrode layer; removing a part of the stack structure and a part of the first initial electrode layer to form a second capacitor hole, with a remaining part of the first initial electrode layer serving as a first electrode layer, where the first electrode layer, the second electrode layer, and the third electrode layer form a lower electrode; and forming a dielectric layer and an upper electrode in the second capacitor hole, where the dielectric layer covers the lower electrode, and the second capacitor hole is filled with the upper electrode.

[FIG. 2M]